Polaron transport and lattice dynam ics in colossal magnetoresistance manganites

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B ased on the model combining the spin double exchange and the lattice polaron, we have studied the colossalm agnetoresistance phenom ena observed in perovskite manganites $R_{1-x}A_{x}M$ nO₃. First, e ects of both the double exchange and the electron-phonon interaction on the transport property are investigated. We have evaluated the tem perature dependent resistance and the magnetoresistance using the K ubo form ula, and exam ined the crossover from tunneling to hopping regime of sm all polarons. Second, e ects of the double exchange interaction on the lattice degree of freedom are explored. It is found that both the hardening of the phonon frequency and the reduction of the phonon dam ping take place with decreasing the tem perature.

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I. IN TRODUCTION

The "colossal" magnetoresistance (CMR) manganites $R_{1 x} A_x M nO_3$ (R= La, Pr, Nd; A= Ca, Ba, Sr, Pb) have recently attracted considerable attention due to scienti c interest and potential applicability of their very large magnetoresistance (MR) for $0.2 \le x \le 0.5$ [1{3]. The most essential feature of their magnetic and transport behaviors is the existence of metallic conductivity and ferrom agnetism. The magnetic transition at T_c is closely connected with the resistivity peak at T_P corresponding to an insulator metal transition ($T_c = T_P$). The correlation between ferrom agnetism and metallic conductivity in $R_{1 x} A_x M nO_3$ was explained by Zener [4] in terms of the double exchange mechanism. There are mixed valent M n ions (M n³⁺ and M n⁴⁺) as a consequence of hole doping by substituting R^{3+} with A^{2+} . In the double exchange model, conduction electrons in the partially lied e_g levels of the d band are strongly coupled with the tightly bound d electrons in the t_{2g} levels by the on-site H und's coupling, and mediate the ferrom agnetic exchange interaction between the nearest neighbor $S = \frac{3}{2}$ local spins form ed from three d electrons in the core-like t_{2g} levels [4,5].

Transport properties have been studied within the double exchange mechanism in favor of a magnetic polaron [6{8]. Recently, M illis et al. [9] reported that the elective carrier-spin interaction involved in the ordinary double exchange H am iltonian is too weak to produce the magnetic polaron elects. Instead, they suggested lattice polaron elects due to a strong electron-phonon interaction as a necessary additional extension [10]. They investigated a model of electrons, Jahn-Teller coupled to localized classical oscillators, within the dynam ical mean led theory. Roder et al. [11] also examined the combined in uence of the electron-phonon interaction and the double exchange on T_c using the variational wave function techniques. But they could not treat the polaron transport and the lattice dynam ics on an equal footing. In fact, the contribution of the lattice polaron to carrier mobility was pointed out earlier by G oodenough [12].

There are many experimental evidences suggesting in portance of the electron-lattice coupling in manganese oxides [13{17]. Near T_c , dramatic changes are observed in the lattice degree of freedom – the anomalous lattice expansion beyond G runeisen law [14], and the shift of phonon frequency [15{17], which all reject that the lattice is closely related to the electronic and magnetic properties. However, detailed understanding of the interplay between the lattice dynamics and the electronic and magnetic properties remains to be resolved.

In this paper, we have addressed two questions; i) what is the role of the electron-phonon interaction in CMR systems which are known to have the double exchange interaction, and reversely, ii) how the double exchange interaction a ects the lattice dynam ics through the electron-phonon interaction. For these purposes, we rst investigate e ects of both the double exchange and the electron-phonon interaction on transport and magnetic properties. Employing the K ubo form ula, we have determ ined the tem perature dependent resistance and the magnetoresistance, and exam ined the crossover from a metallic tunneling state to an insulating hopping state in the small polaron transport. Second, to characterize the lattice dynam ics in CMR compounds, we have considered the phonon degree of freedom in the presence of the double exchange interaction. We have studied the renorm alization of the phonon frequency and the phonon dam ping constant.

This paper is organized as follows. In section II, we present the model of conduction electrons coupled to phonons as well as the localized ionic spins in terms of the double exchange, whereby the tem perature dependent resistance and the magnetoresistance are evaluated from the Kubo formula. In section III, we exam ine the double exchange

e ects on the lattice degree of freedom . Finally, conclusions follow in section IV .D etailed calculational steps are given in Appendix.

II.POLARON TRANSPORT

Since Zener [4] has proposed an interaction between spins of magnetic ions named "double exchange", Anderson and Hasegawa [5] studied this mechanism in a system of M n ions and a mobile electron with the transfert between two M n ions and the strong intra-atom ic exchange integral J. When J is much larger than t, motion of the mobile electrons in $R_{1 x} A_x M nO_3$ is described by the following double exchange H am iltonian,

$$H_{DE} = \sum_{ij}^{X} t_{ij} \cos \frac{ij}{2} c_{i}^{y} c_{j}; \qquad (1)$$

where the hopping t_{ij} connects neighboring sites, and i_{j} is the angle between the directions of ionic spins at sites i and j. An exact quantum mechanical calculation gives $\cos \frac{ij}{2} = \frac{S_0 + 1 = 2}{2S + 1}$; where S is the spin of a M n ion and S_0 is the total spin of S_i , S_j and the conduction electron spin. In this study, we treat the double exchange part within the mean eld theory following K ubo and O hata [6], in which $\cos \frac{ij}{2}$ is replaced by its therm odynam ic average $hoos \frac{ij}{2}$ i determ ined by m inim izing the free energy of the spin system. Then the propagation of an electron can be described as if it were moving in a mean eld of highly disordered con gurations of ionic spins. This approximation is known to work well at nite temperature, except for the very low temperature region (T OK) where the spin dynam ics becomes important. W ithin the present mean eld theory, the double exchange plays a role, through $h\frac{S_0 + 1 = 2}{2S + 1}$ i (T), of increasing the bandwidth as T decreases below T_c , accompanied by the ferrom agnetic ordering (see Fig. 1 (a)).

In addition to the double exchange, the conduction electrons are scattered by the M n - 0 ionic motions in the $M n 0_6$ octahedra, which gives rise to a very strong electron-phonon interaction. The electron H am iltonian incorporating the electron-phonon interaction is written as,

$$H = thcos_{-2} \overset{X}{i} \overset{X}{c_{1+}^{y}} \overset{X}{c_{1}} + \overset{X}{!}_{q} a_{q}^{y} a_{q} + \overset{X}{c_{1}^{y}} c_{1} e^{iq R_{1}} M_{q} (a_{q} + a_{q}^{y}):$$
(2)

Here we adopt a model in which the single e_g orbital is coupled to phonons assuming the electronically active e_g band to be split, as in Roder et al.'s [11]. The present assumption is expected to be more elective if the model were generalized to include another physics such as the on-site C oulom b interaction, which might remove possible mid-gap states away from the Fermi level [10].

The dc conductivity can be obtained from the optical conductivity (!) by taking the !! 0 limit, and (!) can be determined by using the K ubo formula of the current-current correlation function,

$$(!) = \frac{1 e^{!}}{2!} \int_{1}^{Z_{1}} de^{i!} h J^{Y}() J(0) i;$$
(3)

Since the current operator J in narrow band system s is given by

$$J = ithcos \frac{1}{2} ie \int_{j}^{X} c_{j+}^{y} c_{j}; \qquad (4)$$

explicitly involves the four-site correlation function,

$$= \frac{1}{2} t^{2} h \cos \frac{1}{2} i^{2} e^{2} \int_{0}^{X} \int_{0}^{X} \int_{0}^{X} \int_{1}^{X} dh c_{j}^{v} () c_{j+} () c_{j^{0}+0}^{v} c_{j^{0}} i:$$
(5)

In the isotropic case, the resistivity corresponds to the inverse of , = 1 = .

To evaluate , let's consider the well-known polaron canonical transformation [18]; $H = e^{S}He^{S}$ with $S = \int_{jq} c_{j}^{v} c_{j}e^{je^{iq}R_{j}} \frac{M_{q}}{!_{\sigma}} (a_{q} - a_{q}^{v})$: The transformed Ham iltonian H is given by

$$H = thcos_{2} \overset{X}{i} \begin{array}{c} c_{j+}^{v} c_{j} X_{j+}^{v} X_{j} + & & X \\ j & & q \end{array} \begin{array}{c} X & & X \\ c_{j}^{v} a_{j}^{q} a_{q}^{q} & & c_{j}^{v} c_{j} c_{j}; \end{array}$$
(6)

with $X_j = \exp \left[\begin{array}{cc} h_P & i \\ q e^{iq R_j} \frac{M_q}{!_q} (a_q & a_q^Y) \right]$ and $= \left[\begin{array}{cc} P & \frac{M_q^2}{!_q} \\ q \frac{M_q^2}{!_q} \end{array} \right]$. Inserting $e^S e^S = 1$ between each electron operator in Eq.(5), and using $e^S c_j e^S = c_j X_j$ and $e^S c_j^Y e^S = c_j^Y X_j^Y$, one gets

$$= \frac{1}{2}t^{2}h\cos_{2}i^{2}e^{2}XX (^{0})^{X}_{jj^{0}} (^{0})^{j}_{1} dhc_{j}^{y}()c_{j+}()c_{j^{0}+}^{y}c_{j^{0}}X_{j}^{y}()X_{j+}()X_{j^{0}+}^{y}X_{j^{0}+}X_{j^{0}}i:$$
(7)

The intricate correlation function of Eq.(7) should be evaluated under the transform ed H am iltonian H. Calculation can be further simplified with an approximation replacing the first term of Eq.(6) by thos $\frac{1}{2}i \int_{j} hX_{j+}^{Y} X_{j}ic_{j+}^{Y} c_{j}$: This approximation is quite reasonable in view of that the coherent band-like motion of the polarons arises from the quantum mechanical tunneling between sites without changing the phonon numbers, which is governed by the matrix elements of $\ln_q X_{j+}^{Y} X_j ic_{j+}^{Q} (19)$. With increasing T, the polaron bandwidth decreases exponentially due to the term $hX_{j+}^{Y} X_j i((T))$,

$$(T) = \exp\left[\int_{q}^{X} j_{q} f(N_{q} + 1 = 2)\right];$$
(8)

where $u_q \quad (M_q=!_q) (e^{iq} \quad 1)$ (see Fig. 1(b)). Under the above approximation, the mean eld scheme of K ubo and O hata [6] can be generalized to include the phonon contributions which drastically reduce the magnetic transition temperature T_c [11], whereas the temperature dependent behavior of $hoos_2i((T))$ does not appreciably change.

W ith the approximate H am iltonian H incorporating both (T) and (T), the complicated four-site correlation function in Eq.(7) can be disentangled into hc_j^y () c_{j+} () $c_{j^{0+}}^y$, $c_{j^0}hX_j^y$ ()X_{j+} ()X_{j^{0+}}, X_{j^0}i. These correlation functions and can be evaluated in the straightforward fashion. Detailed calculational procedures are provided in Appendix. From Eq.(A12), the dc conductivity is given as follows,

$$= \frac{1}{2} t^{2} (T)^{2} e^{2} \sum_{\substack{0 \\ jj0 \\ k_{1}k_{2}}}^{X} (n_{k_{1}})^{X} n_{k_{1}} (1 n_{k_{2}}) e^{ik_{1} \kappa_{j} \kappa_{j0}} e^{ik_{2} \kappa_{j} \kappa_{j0} + \cdots + \cdots + \cdots + \cdots + \cdots + m} e^{(r_{k_{1}} \kappa_{k_{2}})^{2} - 2T} e^{(r_{k_{1}} \kappa_{k_{2}})^{2} - 4 (j;j^{0}; \tilde{r})^{0} + 1} e^{(T)} e^{(j;j^{0}; \tilde{r})^{0}; T)} [= (j;j^{0}; \tilde{r})^{0}; T)]^{1-2};$$
(9)

with a renorm alized polaron band, $t_{k} = t$ (T) (T) $P = e^{ik}$. Explicit expressions of $(j; j^{0}; ; ; *^{0}; T)$, (T), and $(j; j^{0}; ; *^{0}; T)$ are given in Appendix. K exping in m ind that the auto-correlation function is m ost dom inant for $j = j^{0}$ and $\tilde{t} = *^{0}$, is m ore simply obtained in the following form

$$= \frac{1}{2} t^{2} (T)^{2} e^{2} N z n_{\tilde{k}_{1}} (1 n_{\tilde{k}_{2}}) e^{(t_{\tilde{k}_{1}} t_{\tilde{k}_{2}})^{-2} T} e^{(t_{\tilde{k}_{1}} t_{\tilde{k}_{2}})^{2} - 4 (T)} e^{(T)} e^{(T)} (T) (T)^{1-2}$$
(10)

Here z is the num ber of the nearest neighbors, n_{k} and N_{q} are the ferm ion and boson distribution function, respectively, and (T), (T), and (T) are also given by

$$(T) = \int_{q}^{X} j_{q} f(1 + 2N_{q});$$
(11)

$$(\mathbf{T}) = \sum_{q}^{X} \left[{}_{q}^{2} \mathbf{j}_{q} \mathbf{j}_{q}^{2} \mathbf{N}_{q} (\mathbf{N}_{q} + 1) \right]^{1=2};$$
(12)

$$(\mathbf{T}) = 2 \int_{q}^{X} j \mu_{q} f [\mathbb{N}_{q} (\mathbb{N}_{q} + 1)]^{1-2}:$$
(13)

Now let's investigate the qualitative behavior of .0 ne can carry out the num erical calculation of Eq.(10), assuming the simple square density of states (DOS) D(),

D () =
$$\frac{N(1 x)}{F}$$
; $\frac{W}{2}$ $\frac{W}{2}$: (14)

Here the bandwidth W is given by w (T) (T) (w is the bare electron bandwidth and estimated to be $w = 12 \pm j$ 2eV from the band structure calculation), and the Fermi energy _F is w (T) (T)(1 x) with x being the doping concentration. These treatments of DOS are based on the assumption that only the lower one of the split e_g bands is active. We also assume that the most relevant phonon mode is the optical mode ($!_0$) which might be involved in the Jahn-Teller coupling.

Numerical results for the resistivity are provided in Fig.2. Two dashed lines represent resistivities of the polaron only model with given bandwidths of t_{up} (= w (T)) and t_{low} (= 0:75w (T)). Here t_{up} and t_{low} correspond, respectively, to upper and lower limits of the double exchange factor (T). In both cases, 's exhibit peaks as a function of T, and the larger band width t_{up} yields a smaller with a peak at higher temperature. The resistivity peak as a function of T corresponds to the crossover from a quantum tunneling of the metallic phase to a self-trapped small polaron hopping of the insulating phase. Such features are characteristics of polaron systems, which are indeed observed in m any oxide systems. In the high T limit, the resistivity has a therm all activation form of exp($_g=T$), characteristic of the sem iconducting phase [18]. Now taking the double exchange into account, the polaron bandwidth increases with decreasing T due to (T), and accordingly the resistivity is given by the solid line (in Fig.2) with a peak at T_c connecting the two polaron resistivity curves. This gure clearly demonstrates that the sem iconducting behavior above T_c is attributed to self-trapped lattice small polarons, and that the rapid fall-o in the resistivity below T_c is attributed to the double exchange mechanism in addition to the lattice polaron e ect. Thus, the combined model of the double exchange and the polaron provides a good description of the resistance anom ally observed in the experim ent. The coincidence of the resistivity peak position T_P with T_c originates from the mean eld treatment of (T) which neglects the uctuation in the hopping of conduction electrons.

E ects of the external magnetic eld can also be taken into account in (T) through the modi ed free energy due to the magnetic eld. The behaviors of the MR's are shown in the inset of Fig. 2. With increasing the eld intensity, the resistivity decreases and the peak position shifts to a higher T, and so the negative MR results. These results are quite consistent with the experimental observations. The MR peak $T_{M,R}$ is located near the resistivity peak T_P . In fact, $T_{M,R}$, T_P , and T_c are the same in the present mean eld treatment. It should be noticed that the magnitudes of the MR's in the gure are not large enough to explain the experimental CMR data quantitatively, suggesting that additional treatments might be required. One possibility is to incorporate the half-metallic nature of the ferrom agnetic manganites [20,21], which is expected to suppress largely the spin-disorder scattering under the external magnetic eld.

III. LATTICE DYNAM ICS

A sm entioned before, the phonon frequency becomes hardened as T decreases below T_c [15{17]. Interestingly, the phonon hardenings are observed for both optical and acoustic phonons in these systems. These frequency shifts are considered to be due to the change in the electron screening as T is lowered below T_c . The hardening occurs in the m etallic region (T $< T_c$), i.e., in the band-type tunneling regime where Rayleigh-Schrödinger perturbation theory is valid [18]. Therefore it is expected that the change of the bandwidth due to the double exchange factor (T) m odi es the electron screening below T_c . Note that the previous approximation for the canonically transformed H am iltonian H corresponds to neglecting the phonon frequency renorm alization, which seem s to be too sm all to cause any appreciable change in the transport properties. In the m etallic regime, the screening of the conduction electrons will be m ore easily described by the original H am iltonian H of Eq.(2) rather than the polaron H am iltonian H of Eq.(6).

The renorm alized phonon frequency k_q and the dam ping constants $_q$ can be obtained from the following equation [22]

$$(\dot{t}_{q} \quad \dot{i}_{q})^{2} = !_{q}^{2} \quad 2!_{q} M_{q} f^{2} F (q; \dot{t}_{q} + i0^{+}); \dot{t}_{q} \quad q;$$
(15)

where the electron screening function F (q; $\frac{1}{2}$) is given by

$$F (q; t_{q}) = \begin{cases} X & \frac{n_{k} & n_{k+q}}{(T)(t_{k+q} & t_{k}) & t_{q}}; t_{k} = t \\ \end{cases} t_{k} = t e^{ik}$$
(16)

The real part of both sides of Eq.(15) yields

$$t_{q}^{2} \prime t_{q}^{2} = 2 t_{q} M_{q} f \frac{1}{(T)} \sum_{k}^{X} \frac{n_{k} n_{k+q}}{t_{k+q} t_{k}} :$$
 (17)

It is in portant to note that the term $\begin{bmatrix} r \\ q \\ n_k \\ n_{k+q} \end{bmatrix} = (t_{k+q} \\ t_k \end{bmatrix}$ has very weak temperature dependences (C + O (T=E_F)², E_F being the Ferm i level determined from t_k). Hence the T-dependence of t_q comes dominantly from (T), and Eq.(17) can be written as $t_q = !_q (1 = (T))^{1=2}$, where contains all the T-independent terms. An explicit calculation of is not available, but the order of its magnitude should be very small, O ($M_q f = (!_q E_F)$) O (10²). In Fig. 3(a), T-dependent behaviors of t_q are plotted with respect to the external magnetic eld strength H, and compared with the available experiment [16] in the inset. It is seen that the frequency hardenings with decreasing T and with increasing H are qualitatively well explained. How ever, it is also apparent that some deviations exist between calculational and experimental results, particularly, near T_c . These discrepancies might be ascribed to the mean eld treatment of (T). Including spin correlation e ects in calculating (T) is expected to improve the agreement. It should also be noted that the phonon frequency hardening of Eq.(17) would be valid for both acoustic and optical phonon m odes consistently with the experiments, because we have assumed the general form of the electron-phonon interaction in Eq.(2).

Taking the imaginary part for both sides of Eq.(15), one gets the phonon dam ping parameter q,

$$2_{q} t_{q} = 2!_{q} M_{q} f \frac{1}{(T)} m_{k} \frac{n_{k}}{t_{k+q}} t_{k} \frac{n_{k}}{t_{q}} (T) i0^{+}$$
(18)

The imaginary part of the screening function is easily calculated by considering a parabolic electron band $t_{k} = t^{P} e^{ik^{-1}} t^{j} j^{2}k^{2}$,

$$2_{q} = 2!_{q} M_{q} \frac{f}{2} \frac{D(E_{F})}{v_{F} q} \frac{1}{(\Gamma)^{2}}; \qquad (19)$$

where D (E_F) and v_F are determined from the parabolic band, $j_{\rm cj}^2 k^2$. In Fig. 3(b), T-dependent behaviors of $_{\rm q}$ are presented. Our results predict that the phonon damping parameter decreases with decreasing T, in plying that the phonon is more sharply de ned below T_c. This feature in CMR systems is quite di erent from conventional observations of increased phonon damping parameter below T_c for magnetic or strongly correlated systems. To our know ledge, no experimental reports are available yet on the phonon damping parameters. We think that the sound attenuation experiment will provide a better understanding of the nature of the electron-phonon interaction in CMR system s.

IV . C O N C LU S IO N S

We have extended the double exchange m odel to incorporate the strong electron-phonon interaction, and investigated transport and m agnetic properties of CMR m anganese oxides $R_{1 x} A_x M nO_3$. We have found that the sem iconducting behavior in m anganites above T_c is attributed to the e ect of self-trapped lattice small polarons, and that the rapid fall-o in the resistivity below T_c is attributed to the combined e ect of coherent lattice polarons and the increased bandwidth via the double exchange m echanism accompanied by the ferrom agnetic ordering of m agnetic ions. Further, we have explored e ects of the double exchange on the phonon degrees of freedom. The tem perature dependent hardening of the phonon m ode frequency observed in experiments is well described, and the reduction of the phonon dam ping constant is predicted below T_c .

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APPENDIX: CALCULATION OF dc CONDUCTIVITY

To evaluate the dc conductivity , one should evaluate correlation functions of electrons and phonons under the H am iltonian H \cdot D e ning simply and 0 as

$$= e^{iq R_{j}} (e^{iq^{\sim}} 1)^{\frac{M_{q}}{!_{q}}}; \quad {}^{0} = e^{iq R_{j}^{0}} (e^{iq^{\sim}} 1)^{\frac{M_{q}}{!_{q}}}; \quad (A1)$$

X $_{j}^{y}$ ()X $_{j+}$ ()X $_{j^{0}+}^{y}$ $_{0}$ X $_{j^{0}}$ is given by

$$X_{j}^{Y}()X_{j+}()X_{j^{0}+}^{Y} X_{j^{0}+}^{Q}X_{j^{0}} = \begin{cases} Y \\ e^{\frac{1}{2}(j f^{2}+j f^{0})^{2}} e^{a_{q}^{Y}e^{it}q} \\ q \end{cases} e^{a_{q}e^{it}q} e^{a_{q}e^{it}q} e^{-a_{q}^{Y}e^{it}q} e^{-a_{q}^{Y}e^{it}q} e^{-a_{q}^{Y}e^{it}q} \end{cases}$$
(A2)

Using $e^{a_{q}e^{i!_{q}}}e^{0_{a_{q}}^{y}}=e^{0_{a_{q}}^{y}}e^{a_{q}e^{i!_{q}}}e^{0_{e^{i!_{q}}}}$, we see

$$X_{j}^{Y}()X_{j+} ()X_{j^{0}+} X_{j^{0}+} X_{j^{0}} = Y_{q} e^{\frac{1}{2}(j j^{2}+j 0^{2} j^{2})} e^{-0 e^{i! q}} e^{-a_{q}^{Y}} e^{-a_{q}};$$
(A3)

where $e^{i!_q}$ ⁰. Under the noninteracting phonon H am iltonian, the therm odynam ic average of $he^{a_q^y}e^{a_q}i$ is given by [18]

he
$$a_{q}^{y}e^{a_{q}}i=e^{jj^{2}N_{q}}; N_{q}=\frac{1}{e^{!_{q}}}; A_{q}=\frac{1}{e^{!_{q}}}; A_{$$

Then hX $_{j}^{\rm Y}$ ()X $_{j^+}\,$ ()X $_{j^{0}+}^{\rm Y}\,_{_{0}}$ X $_{j^{0}}$ is obtained as follows

$$hX_{j}^{Y}()X_{j+}()X_{j^{0}+}^{Y}()X_{j^{0}+}^{Y}()X_{j^{0}}i = \exp[(R_{j} R_{j^{0}}; ; ;];$$
(A5)

$$(\tilde{R}_{j} \quad \tilde{R}_{j^{0}}; \tilde{r}; \tilde{r}^{0};) = \begin{cases} X & j \mu_{q} f(1 + 2N_{q}) \\ X & 2 \\ 2 & v_{q} (j; \tilde{r}) v_{q} (j^{0}; \tilde{r}^{0}) N_{q} (N_{q} + 1)]^{1 = 2} \cos [!_{q} (+ i\frac{1}{2})];$$

$$(A 6)$$

where $u_q = M_q = !_q$ (e^{iq} 1) and v_q (j; \sim) $M_q = !_q$) $e^{iq R_j}$ (e^{iq} 1).

The electron four-site correlation function hc_j^y () c_{j+} () $c_{j^0+}^y \circ c_{j^0}i$ is easily evaluated from the Ham iltonian H which transformed into the K-space,

$$hc_{j}^{Y}()c_{j+}()c_{j^{0}+0}^{Y}c_{j^{0}+0}c_{j^{0}}i = \sum_{k_{1};k_{2}}^{X} n_{k_{1}}(1 n_{k_{2}})e^{i(t_{k_{1}} t_{k_{2}})}e^{i(t_{k_{1}} t_{k_{2}})}e^{i(t_{k_{2}} t_{k$$

where the renorm alized polaron band t_{k} is given as t (T) hX $\frac{y}{j+}$ X $_{j}i^{P}$ e^{ik~}.

The time integral of the correlation functions, Eq.(7) can be performed by the saddle point approximation. In the vicinity of the saddle point, the integrand becomes just a Gaussian,

$$(\hat{R}_{j} \quad \hat{R}_{j^{0}}; \hat{r}_{j^{-}}; \hat{r}_{j}^{0};)' \quad (T) \qquad (j; j^{0}; \hat{r}_{j}; \hat{r}_{j}^{0}; T) + (j; j^{0}; \hat{r}_{j}; \hat{r}_{j}^{0}; T) z^{2}; z = + i = 2;$$
(A8)

where (T), $(j; j^0; \tilde{j}; 0; \tilde{j}; T)$, and $(j; j^0; \tilde{j}; \tilde{j}; T)$ are, respectively, given by

$$(T) = \int_{q}^{X} j_{q} j^{2} (1 + 2N_{q});$$
 (A9)

$$(j; j^{0}; ; ; {}^{0}; T) = 2 \sum_{q}^{X} v_{q}(j;) v_{q}(j^{0}; {}^{0}) N_{q}(N_{q} + 1)]^{1=2};$$
(A10)

$$(\mathbf{j};\mathbf{j}^{0};\mathbf{\tilde{r}};\mathbf{\tilde{r}}^{0};\mathbf{T}) = \bigvee_{q}^{X} \left\{ {}_{q}^{2} \mathbf{v}_{q}(\mathbf{j};\mathbf{\tilde{r}}) \mathbf{v}_{q}(\mathbf{j}^{0};\mathbf{\tilde{r}}) \mathbb{N}_{q}(\mathbf{N}_{q}+1) \right\}^{1=2} :$$
 (A 11)

>From Eqs.(7), (A 5), and (A 7), the dc conductivity is evaluated and obtained as

$$= \frac{1}{2} t^{2} (T)^{2} e^{2 X} (r^{0})^{0} n_{\mathfrak{K}_{1}} (1 n_{\mathfrak{K}_{2}}) e^{i\mathfrak{K}_{1} \mathfrak{K}_{1} \mathfrak{K}_{10}} e^{i\mathfrak{K}_{2} \mathfrak{K}_{1} \mathfrak{K}_{10} + \cdots + 0} e^{i\mathfrak{K}_{1} \mathfrak{K}_{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{2} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{2} (r^{0})^{2}} e^{i\mathfrak{K}_{2} \mathfrak{K}_{1} \mathfrak{K}_{2} (r^{0})^{2}} e^{i\mathfrak{K}_{2} \mathfrak{K}_{1} \mathfrak{K}_{10} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{10} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{10} (r^{0})^{2}} e^{i\mathfrak{K}_{2} \mathfrak{K}_{1} \mathfrak{K}_{10} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{10} (r^{0})^{2}} e^{i\mathfrak{K}_{2} \mathfrak{K}_{1} (r^{0})^{2}} e^{i\mathfrak{K}_{2} \mathfrak{K}_{1} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{10} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{1} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{1} (r^{0})^{2}} e^{i\mathfrak{K}_{1} \mathfrak{K}_{1} (r^{0})^{2}} e^{i\mathfrak{K}_{1} (r^{0})^{$$

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FIG.1. Bandwidths (hopping parameters in unit oft) as a function of the temperature. (a) E ect of the double exchange inperaction, t (T); ((T) $hoos_2$ -i). (b) C om bined e ect of the double exchange and the electron-phonon interaction, t (T) (T). _g ju_g $j^2 = 4:5$ is taken.

FIG.2. The resistivity of the polaron only model (two dashed lines) and the combined model of the polaron and double exchange (solid line). In the polaron only model, t_{up} and t_{low} are the bandwidths corresponding to the the upper and lower limiting value of $hoos_{\overline{2}}$ i, respectively. Galculations are performed for the parameters, x = 0.3, $w = 64T_c$ 1:1eV, $!_0 = 5T_c$ 0:08eV assuming T_c 200K, and $_q ju_q f = 6$. The inset presents the resistance behaviors with H = 0T, 4.8T, and 9:6T.

FIG.3. (a) The phonon frequency shifts $(\ddagger_q(T) + \ddagger_q^c) = \ddagger_q^c$ for various magnetic eld strengths, where $\ddagger_q^c + \ddagger_q(1:1T_c; H = 0T)$. In the inset, the shifts are compared with the experiment (under H = 1T) for $La_{0:7}Ca_{0:3}M nO_3$ (Jeong et al.[6]). In the tting, $T_c = 238K$ is taken from experiments. We have taken = 0:07. (b) The phonon damping constants $_q(T) = \ddagger_q^c$ with $\ddagger_q(1:1T_c; H = 0T)$, are given.







